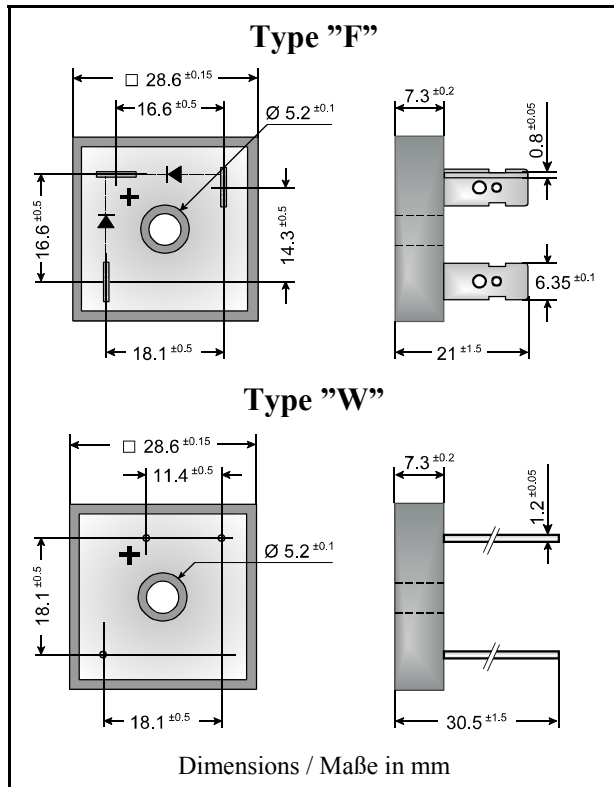


**Silicon-Twin Rectifiers**  
Center tap

**Silizium-Doppeldioden**  
Mittelpunktschaltung



Nominal current 30 A  
Nennstrom

Alternating input voltage 60...250 V  
Eingangswchelsspannung

Plastic case with alu-bottom  
Kunststoffgehäuse mit Alu-Boden

Dimensions 28.6 x 28.6 x 7.3 [mm]  
Abmessungen

Weight approx. 23 g  
Gewicht ca.

Recognized Product – UL-File E175067  
Anerkanntes Produkt – UL Nr. E175067

Compound has classification UL94V-0  
Vergußmasse UL94V-0 klassifiziert

Standard packaging: bulk see page 22  
Standard Lieferform: lose im Karton s.S. 22

**Maximum ratings**

**Grenzwerte**

Type Typ	max. alternating input voltage max. Eingangswchelspannung $V_{VRMS}$ [V]	Repetitive peak reverse voltage Periodische Spitzensperrspannung $V_{RRM}$ [V] <sup>1)</sup>
D30 VC20 F/W	60	200
D30 VC40 F/W	120	400
D30 VC60 F/W	190	600
D30 VC80 F/W	250	800

Repetitive peak fwd. current – Period. Spitzenstrom	$f > 15$ Hz	$I_{FRM}$	80 A <sup>2)</sup>
Peak forward surge current, 50 Hz half sine-wave Stoßstrom für eine 50 Hz Sinus-Halbwell	$T_A = 25^\circ\text{C}$	$I_{FSM}$	300 A
Rating for fusing – Grenzlastintegral, $t < 10$ ms	$T_A = 25^\circ\text{C}$	$i^2t$	450 A <sup>2</sup> s
Isolation voltage – Isolationsspannung	$t = 1$ min	$V_{ISO}$	$> 2000$ V
Operating junction temperature – Sperrschichttemperatur		$T_j$	$-50 \dots +150^\circ\text{C}$
Storage temperature – Lagerungstemperatur		$T_s$	$-50 \dots +150^\circ\text{C}$

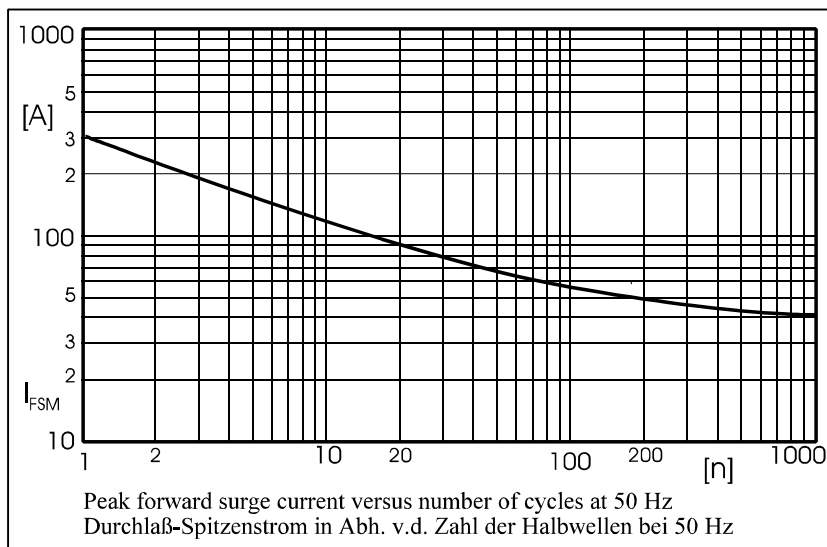
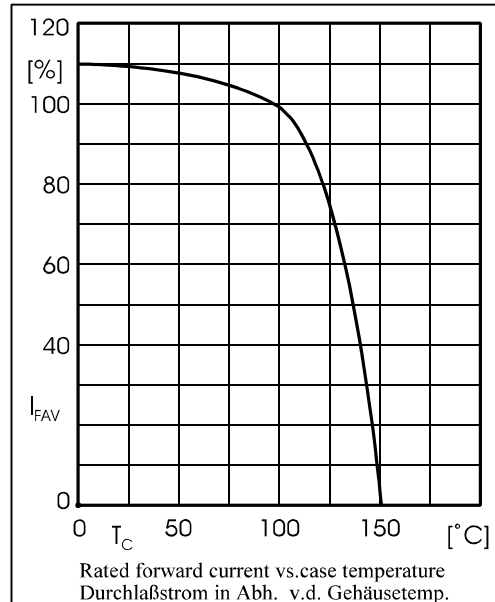
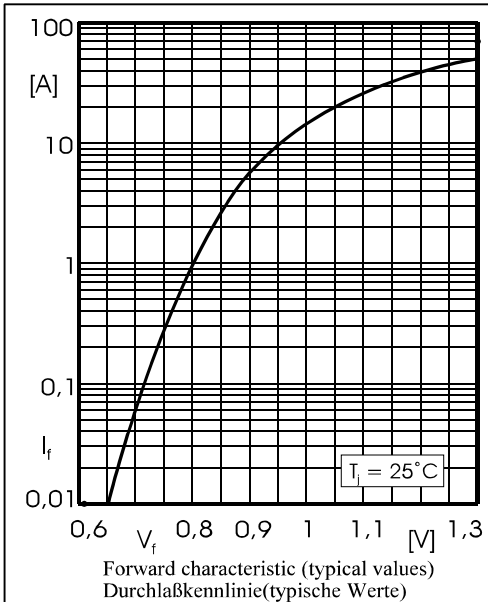
<sup>1)</sup> Valid per diode – Gültig pro Diode

<sup>2)</sup> Max. case temperature  $T_C = 100^\circ\text{C}$  – Max. Gehäusetemperatur  $T_C = 100^\circ\text{C}$

**Characteristics**

**Kennwerte**

Max. current with cooling fin 300 cm <sup>2</sup> Dauergrenzstrom mit Kühlblech 300 cm <sup>2</sup>	$T_A = 50^\circ\text{C}$	R-load C-load	$I_{FAV}$ $I_{FAV}$	30.0 A 26.0 A
Forward voltage – Durchlaßspannung	$T_j = 25^\circ\text{C}$	$I_F = 15\text{ A}$	$V_F$	< 1.05 V <sup>1)</sup>
Leakage current – Sperrstrom	$T_j = 25^\circ\text{C}$	$V_R = V_{RRM}$	$I_R$	< 25 $\mu\text{A}$
Thermal resistance junction to case Wärmewiderstand Sperrschicht – Gehäuse			$R_{thC}$	< 1.0 K/W
Admissible torque for mounting Zulässiges Anzugsdrehmoment		10-32 UNF M 5		18 ± 10% lb.in 2 ± 10% Nm



<sup>1)</sup> Valid per diode – Gültig pro Diode